

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions of claims in the application:

Listing of Claims:

1. (Currently amended) A method for modifying a porous film mainly having Si-O bonds, comprising:

conducting a thermal treatment at a temperature from 100 °C to 600 °C to the porous film without using a metal catalyst, wherein in the thermal treatment, the porous film is brought into contact with an organic silicon compound including one or more Si-X-Si bond unit (wherein X represents O, NR, C_nH_{2n}, or C₆H₄; R represents C_mH_{2m+1} or C₆H₅; m is an integer between 1 and 6; and n is 1 or 2) and two or more Si-A bond units (wherein A represents H, OH, OC_eH_{2e+1} or a halogen atom and may be the same or different within a single molecule; and e is an integer between 1 and 6), the organic silicon compound is a cyclic siloxane, and wherein the contacting is carried out in a gas phase.

2. (Canceled)

3. (Previously presented) The method for modifying a porous film according to claim 1, wherein the porous film before the treatment is a film having mesopores.

4. (Previously presented) The method for modifying a porous film according to claim 1, wherein an average pore diameter of the porous film before the treatment is in a range of 0.5 to 10 nm.

5. (Canceled)

6. (Previously presented) A modified porous film obtained by the method as described in claim 1.

7. (Original) A semiconductor material comprising the modified porous film as described in claim 6.

8. (Original) A semiconductor device in which the semiconductor material as described in claim 7 is used.

9-14. (Canceled)

15. (Previously presented) A modified porous film obtained by the method as described in claim 3.

16. (Previously presented) A modified porous film obtained by the method as described in claim 4.

17. (Canceled)

18. (Previously presented) A semiconductor material comprising the modified porous film as described in claim 15.

19. (Canceled)

20. (Previously presented) A semiconductor device in which the semiconductor material as described in claim 18 is used.